

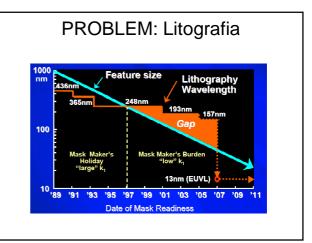
PROBLEM: Podłoża

Krzem 2003,

- wafer 30 mm:
- Wymagane jest nie więcej niż 120 cząstek <100 nm na wafer
- Dokładność polerowania 130 nm

Krzem 2007,

- wafer 30 mm:
- Wymagane jest nie więcej niż 77 cząstek <100 nm na wafer (jak to zmierzyć?)
 Dokładność polerowania 65 nm
- Krzem 2016,
- wafer 450 mm:
- Wymagane jest nie więcej niż 77 cząstek <100 nm na wafer (jak to zmierzyć?)
- Dokładność polerowania 22 nm (jak to zmierzyć?)



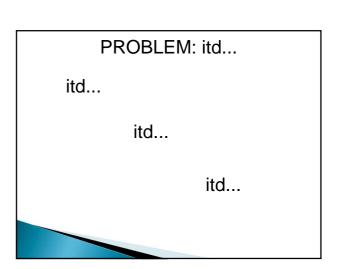
PROBLEM: Litografia

Litografia 2003,

- Długość fali światła 248 nm
- Kanał FET 90 nm:
- Wymagane jest nie więcej niż 2000/m2 <100 nm
- Fluktuacje granic rezystu 7 nm

Litografia 2007,

- Długość fali światła 193 nm (?) 153 nm (?) X-ray (?)
- Kanał FET 35 nm:
 Wymagane jest nie więcej niż 1500/m2 <100 nm
- Prawdopodobnie koniec epoki polimerowych rezystów (cząstki polimerów są zbyt duże!)
- Fluktuacje granic rezystu 3 nm Litografia 2016,
- Długość fali światła X-ray (?)
- Kanał FET 9 nm:
- Wymagane jest nie więcej niż 500/m2 <100 nm
- Fluktuacje granic rezystu 1 nm

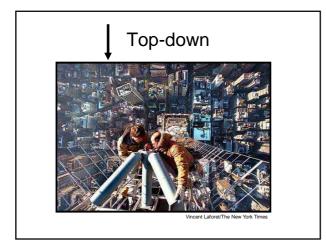


NOWE TECHNOLOGIE

- Przeprojektowanie CMOS (np. wertykalne, FIN, MOSFET z podwójną bramką)
- Urządzenia alternatywne (np. na pojedynczych elektronach)
- Urządzenia hybrydowe (np. FET z nanorurek)
- Nowe architektury (np. samonaprawiające się, defect-tolerance, automaty komórkowe)
- Zupełnie nowe architektury (np. komputery molekularne, komputery kwantowe)





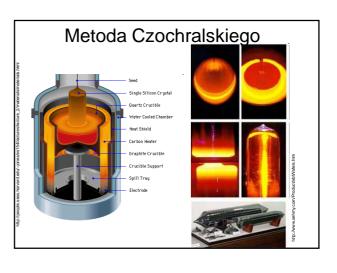








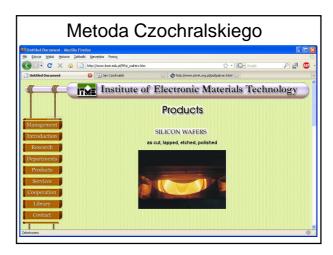


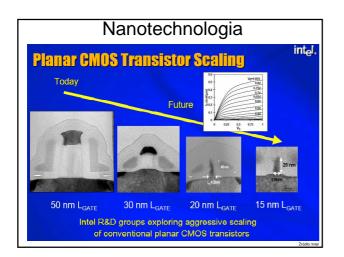




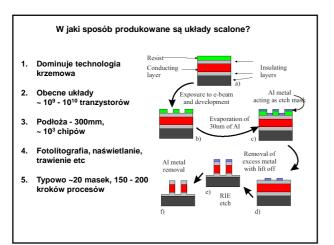


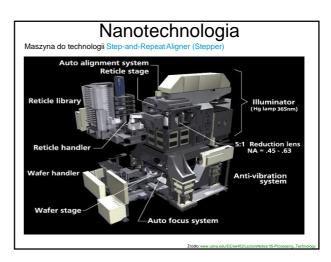


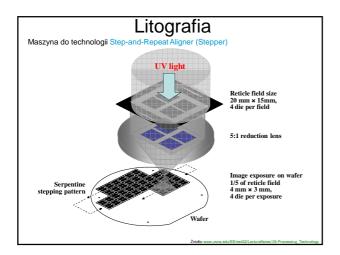


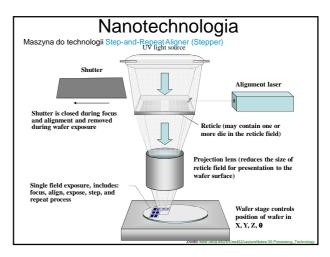


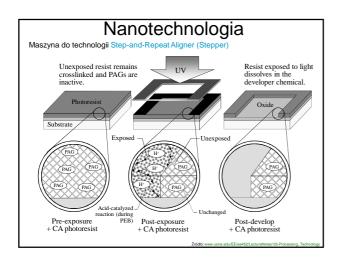
Gdzie jest limit						
SAMSUNG's Digital W Bik Edycja Widok Prze	orld - Press Release - Mozilla Firefox jýži Zeládni Narzędzia Pomoc					
🖕 • 🔿 - 🛃 🛽	0 😭 🗋 http://www.samsung.com/PressCenter/PressRelease/PressRelease.asp?seq=20050912_0000192003					
SAMSUNG	PRODUCTS SUPPORT FEATURES PRESS CENTER ABOUT SAMSUNG Select Country / Region V					
PRESS CENTER V PRODUCT REGISTRATION # COMMUNITY % CART - SEARCH						
Press Release Ilews Archive Photo Archive	Hora > Press Carter > Press Release Press Release 2005 Constraint					
Corporate Films Executive Bios PR Contacts	(12, Sep. 2465 / SEC) SAMSUNG Electronics Develops First 16-Gigabit NAND Memory Using 50-nm Technology for Sharp Jump in Mobile Storage Capacity					
	Secul, Korea, Sept ember 12, 2005 – Sansung Bectronics Co., Ltd., the world leader in advanced memory technology, announced that has developed the world's highest density NAND flash – a 16Gigabit (db) NAND memory device. NAND is the most widely used memory for multi-feature mobile applications.					

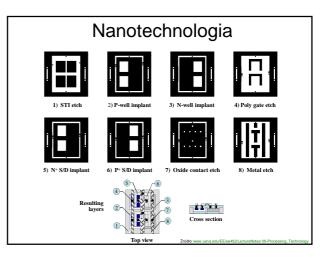


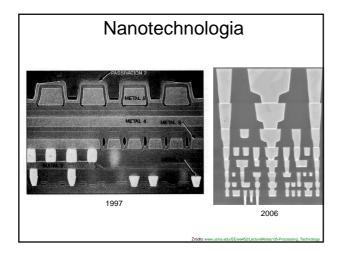


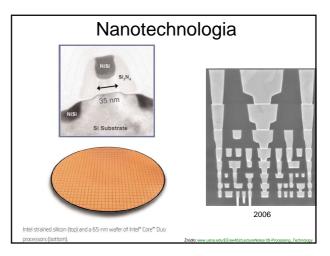




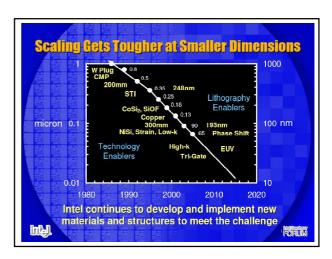


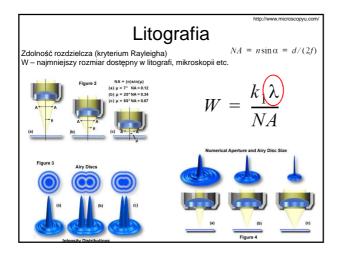


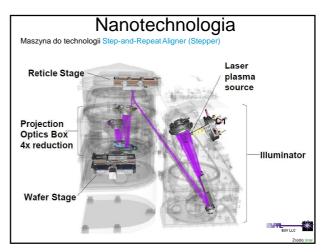




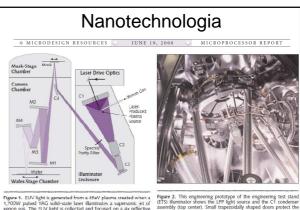






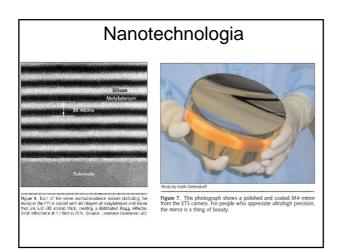


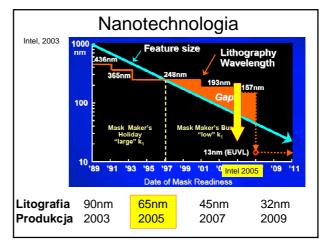


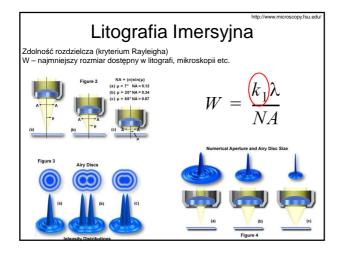


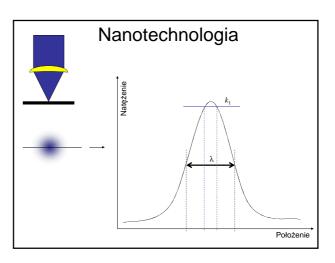
Evolution and environmentation of the service parameters and the service

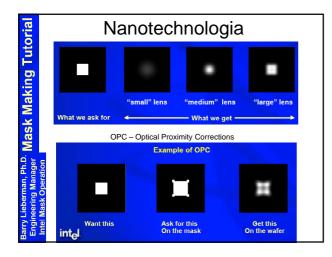
Figure 2. This engineering prototype of the engineering test stant (ETS) illuminator shows the LPP light source and the C1 condense asembly (top cerele). Small trapecidally shaped doors protect th denser weldment, which also holds C2 and C3, is obtained from the environmental chamber to eliminate motion and vibration from the vacuum pumps, (Potolo courtey of standa kational Lab)

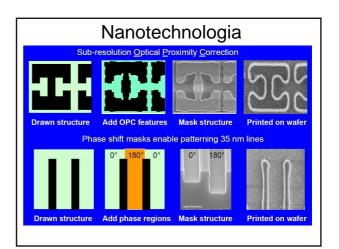


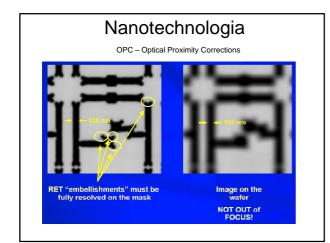


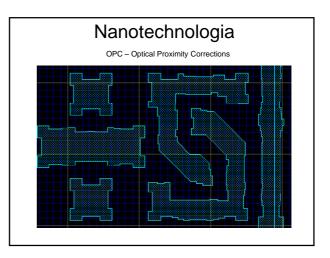


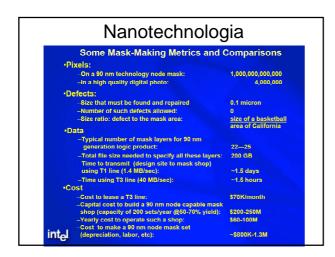


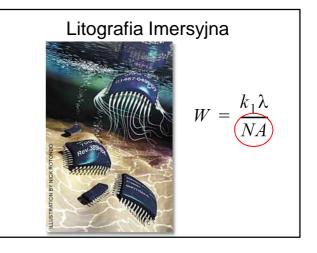


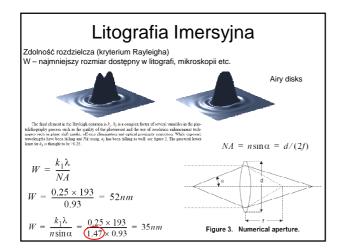


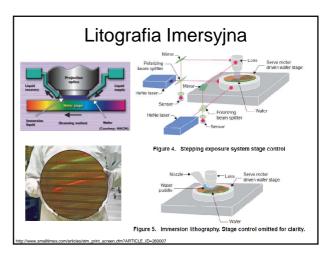


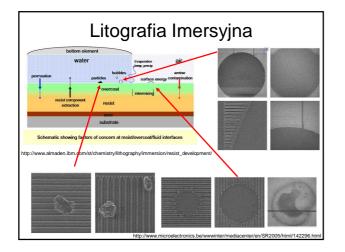








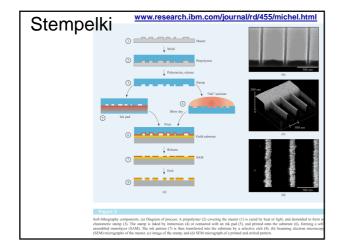


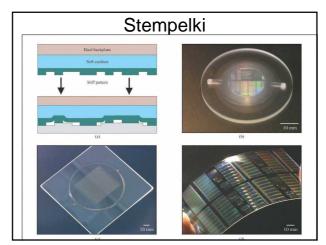




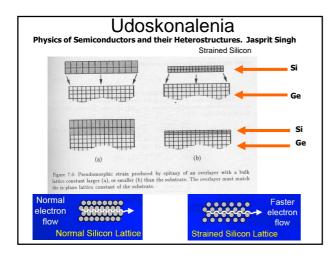


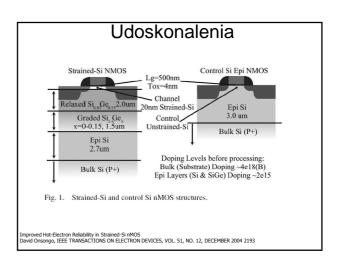


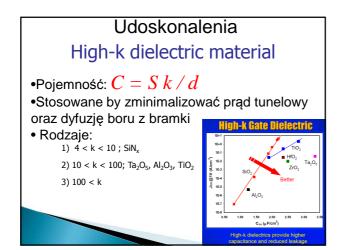


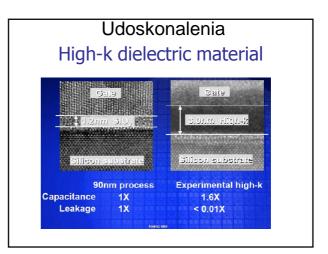


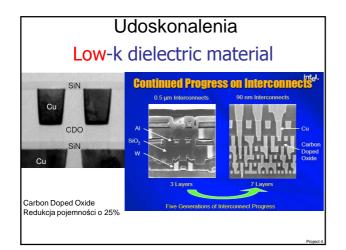


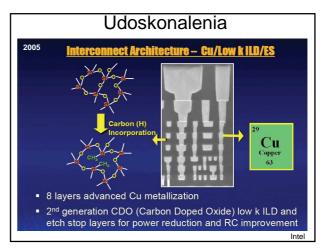


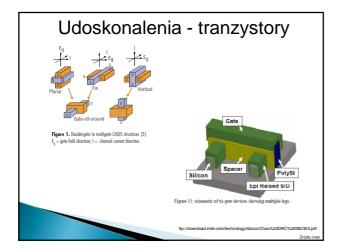


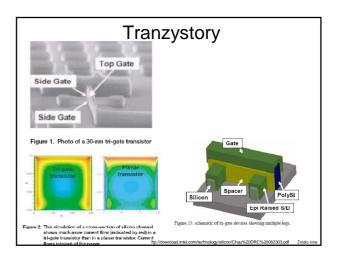


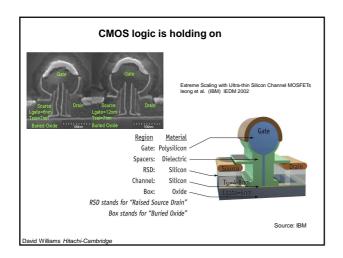












Gdzie jest limit Scaling problems					
	FEATURE	LIMIT	REASON		
	Oxide Thickness	2.3 nm	Leakage (I _{GATE})		
	Junction Depth	30 nm	Resistance (R _{SDE})		
	Channel Doping	V _T =0.25 V	Leakage (I _{OFF})		
	SDE Under Diffusion	15 nm	Resistance (R _{INV})		
	Channel Length	0.06µm	Leakage (I _{OFF})		
	Gate Length	0.10µm	Leakage (I _{OFF})		
	2003		SDE Source-D	rain Extensions	

